



Fundamental Research on Infrared Photodetectors

University of Illinois



MURI, year started:
2001

December
2001

Research Tasks

HgCdTe Photodetectors-Defects and Interface Issues

Type-II Sb-based Quantum-Cascade Photodetectors

Quantum-Dot Infrared Photodetectors (QDIPs)

Objectives

- Investigate defects in HgCdTe photodetectors
- Design and fabricate novel antimony-based type-II quantum-cascade photodetectors
- Fabricate strain-balanced quantum-dot infrared photodetectors (QDIP) using III-V material systems

Approaches

- Identify structure and point defects (TEM, XPS) and optical characterization of defects (PL, FTIR) in HgCdTe systems
- InAs/InGaSb type-II superlattice photodetector design and fabrication by MBE
- Strain-balanced multiple QDIP structure:
 - Eliminate defects through strain-balanced QDIP structures using tensile

Research Partners

- University of Illinois at Urbana-Champaign
- University of Texas at Austin
- Collaborations with Columbia University and University of Illinois at Chicago

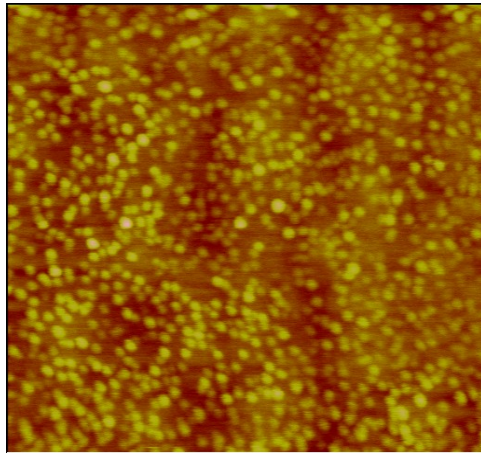
Transition Partners

- DRS IR Technologies, HRL Labs, Appl. Optoelectronics
- ARL, Army Center for Night Vision & Electro-Optics, JPL, Sandia National Lab

Budget: \$2M for 5 years



Quantum Dot Infrared Photodetectors (QDIPs)



AFM image (1x1 μm) of InAs QDs on GaAs

Objectives

- Investigate the growth process and its effects on QD size and density
- Study the effects of barrier thickness and material on QD properties (barrier material: GaAs, InGaP)
- Ultimately use these results to grow high-performance QDIP

Approach

- Use solid-source molecular beam epitaxy (SSMBE) for crystal growth
- Material analysis techniques: AFM, TEM, X-ray diffraction, FTIR analysis, and photoluminescence (PL) measurements
- Use tensile strained barrier materials to compensate the compressively strained QDs to allow for many QD layers in photodetector

Accomplishments

- Achieved successful formation of InAs QDs on GaAs substrates (AFM, TEM and PL)
- Demonstrated QD heterostructures with different barrier materials (PL and X-ray)
- Characterized structure of multiple QD layers (X-ray and TEM)

